

Multiple Oxygen Incorporation Processes in Porous Lanthanum Strontium Ferrite Thick Films Observed by the Curvature Relaxation (κR) Technique

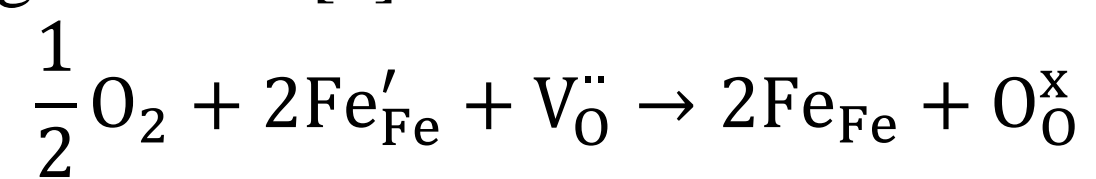


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1. Introduction

$\text{La}_{0.6}\text{Sr}_{0.4}\text{FeO}_{3-\delta}$ (LSF) is a mixed ionic electronic conductor (MIEC) usually used as cathode in Solid Oxide Fuel Cells (SOFCs). Under operating conditions, LSF easily undergoes the following reaction [1]:



The defect reaction expands the lattice, introducing chemical stress into the material. This mechano-chemical reaction can be described by the following equation[2]:

$$\epsilon_c = \alpha_c \Delta \delta$$

where ϵ_c represents the chemical strain, α_c represents the chemical expansion coefficient, and δ represents the oxygen nonstoichiometry. Therefore, with an oxygen partial pressure change, a LSF film on an inert substrate will produce a change in sample curvature as the LSF equilibrates to a new level of oxygen nonstoichiometry.

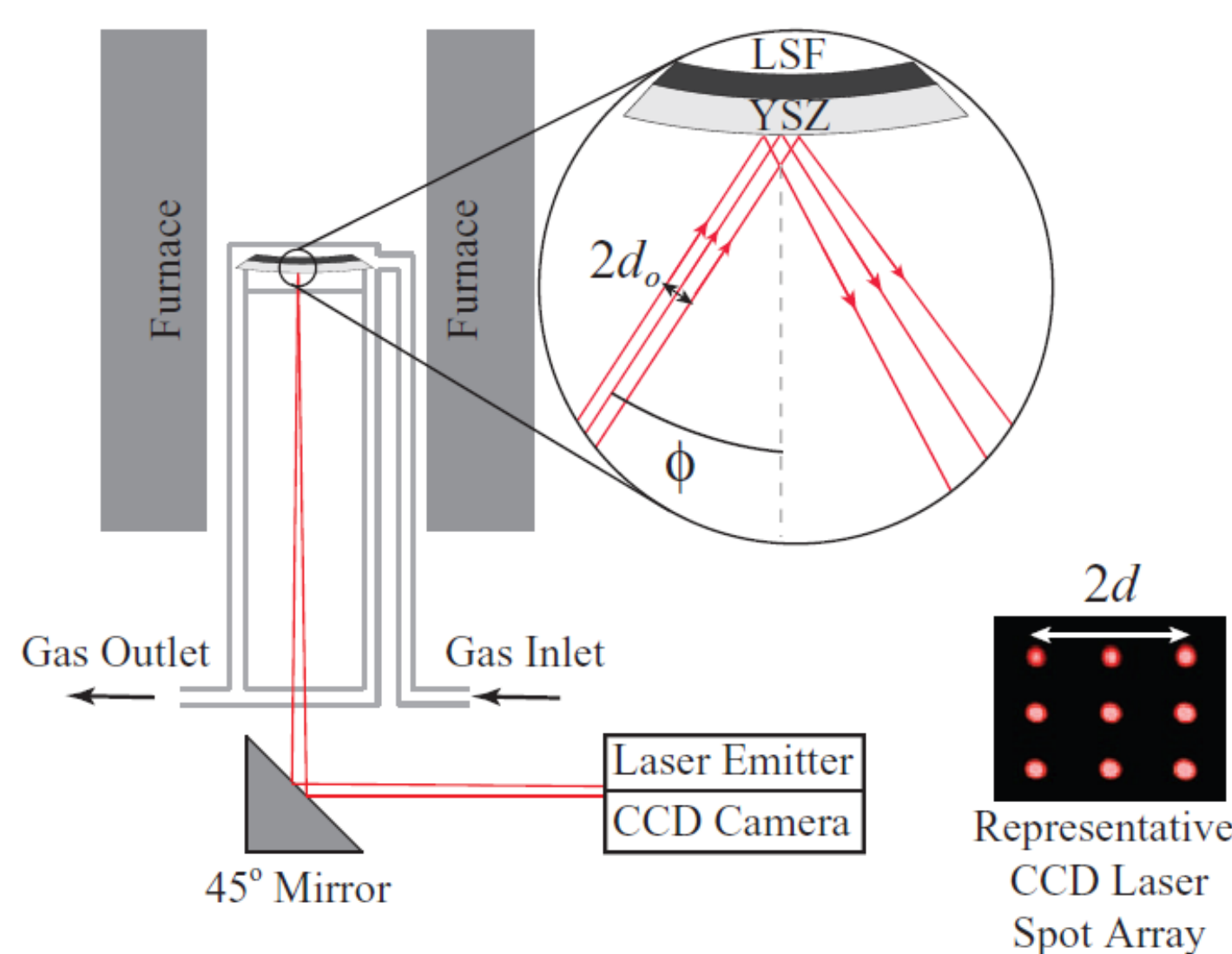
For a dense thin film | inert substrate bilayer sample [3]:

$$\frac{\kappa - \kappa_0}{\kappa_\infty - \kappa_0} = \frac{\delta - \delta_0}{\delta_\infty - \delta_0} = 1 - \exp\left(-\frac{kt}{h_f}\right)$$

For a porous thick film | inert substrate bilayer sample [4,5]:

$$\frac{\kappa - \kappa_0}{\kappa_\infty - \kappa_0} = \frac{\delta - \delta_0}{\delta_\infty - \delta_0} = 1 - \exp\left(-\frac{kt}{\frac{1-V_V}{S_V}}\right) = 1 - \exp\left(-\frac{t}{\tau}\right)$$

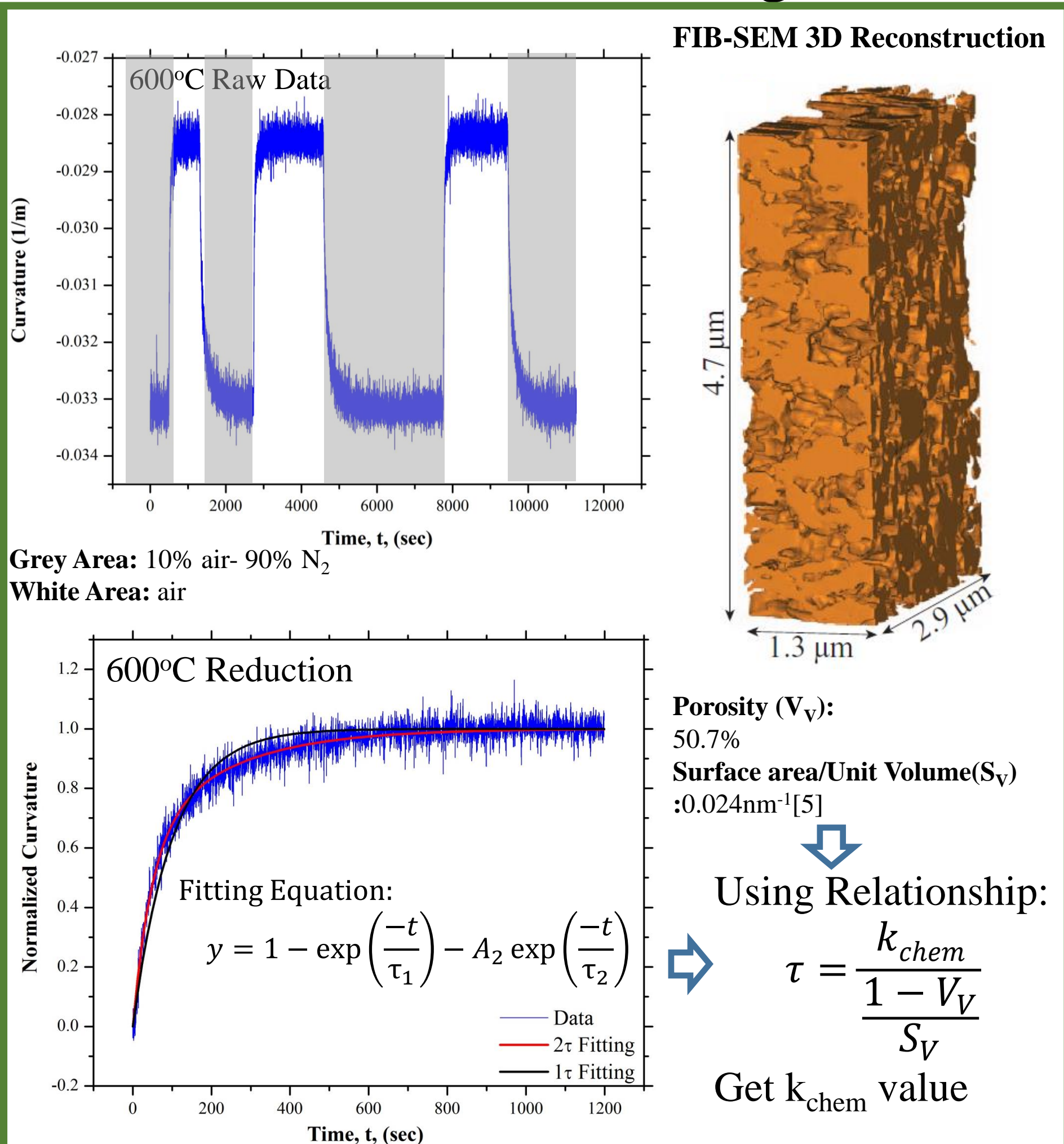
where t represents time; h_f represents the film thickness; κ represents the instantaneous curvature; κ_0 represents the initial curvature; κ_∞ represents the final curvature after pO_2 equilibration; S_V represents the volume specific pore surface area; V_V represents the volume fraction porosity and τ represents the time constant for curvature relaxation.



To measure the curvature from the detector spot spacing[5]:

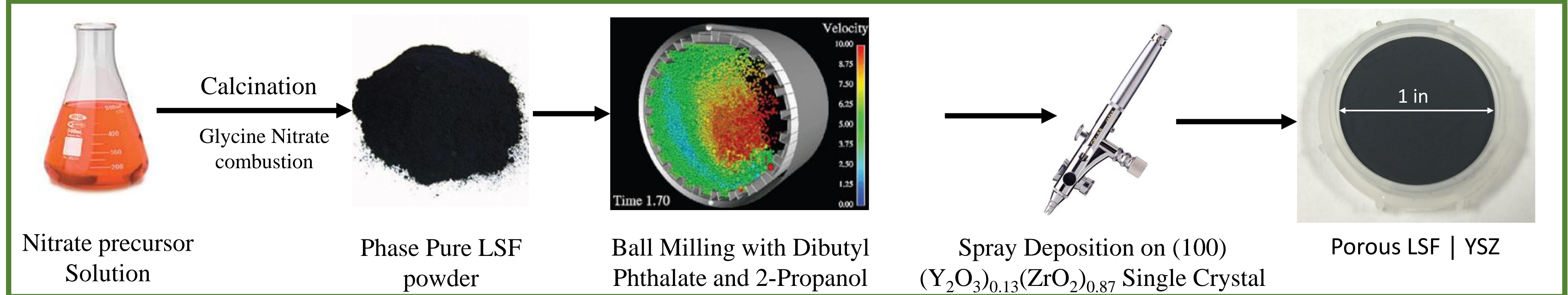
$$\kappa = \left(\frac{\cos\phi}{2L}\right)\left(1 - \frac{d}{d_0}\right)$$

2. LSF κR Data Processing

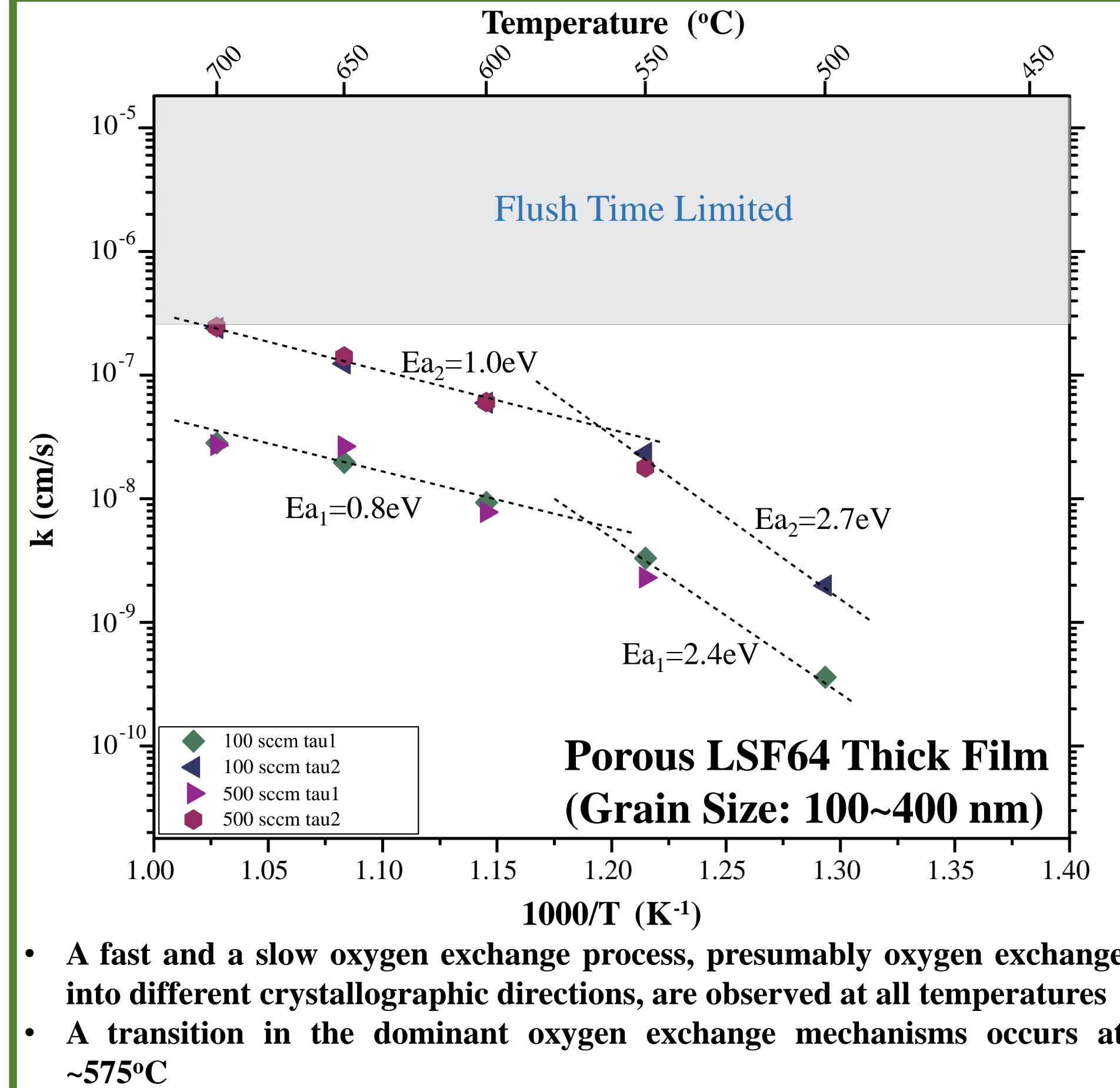


• Two time constants are needed to fit the curvature relaxation curve

3. Porous Thick Film $\text{La}_{0.6}\text{Sr}_{0.4}\text{FeO}_{3-\delta}$ (LSF) Preparation

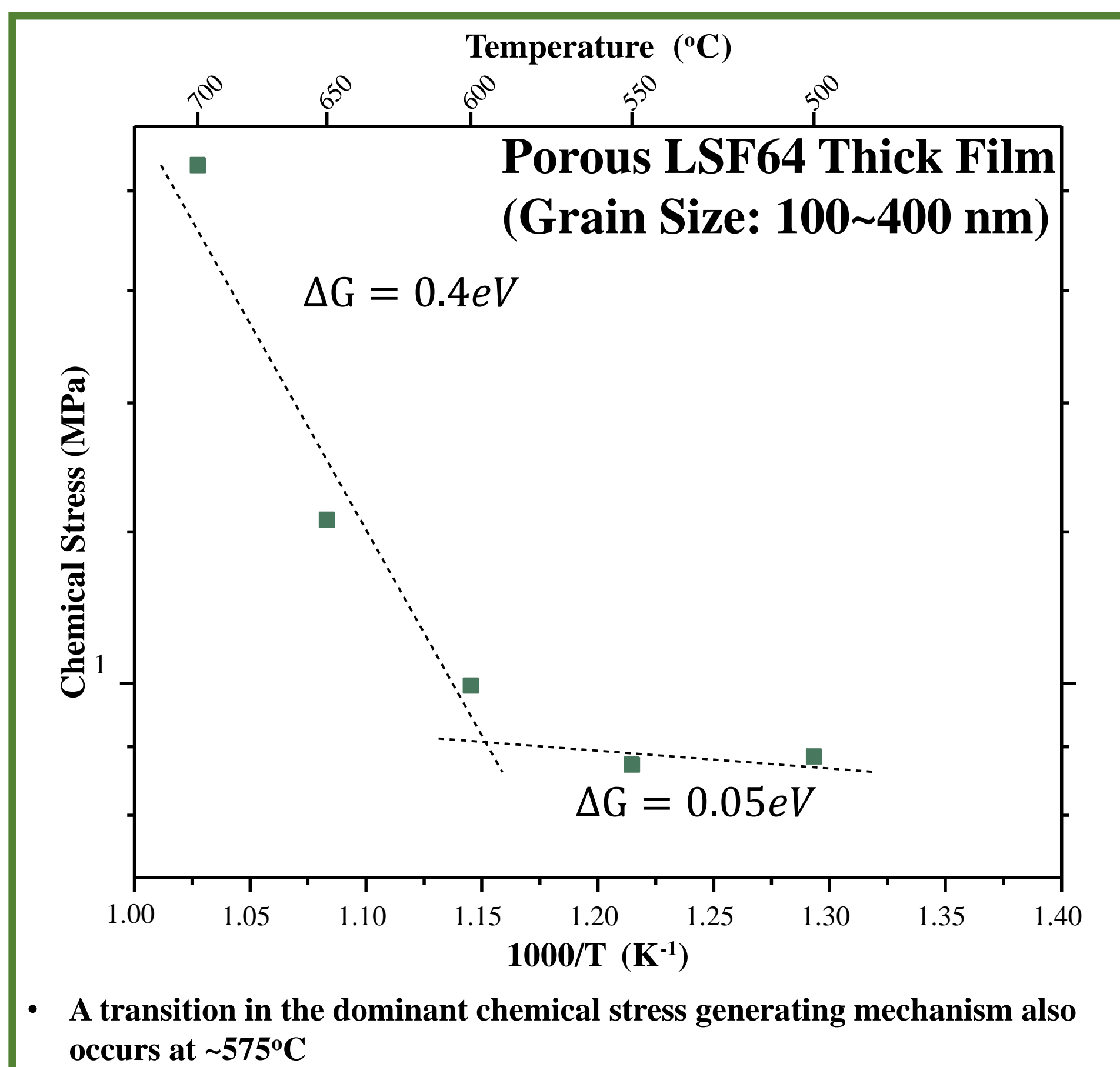


4. LSF k Data vs. Thermal Cycle



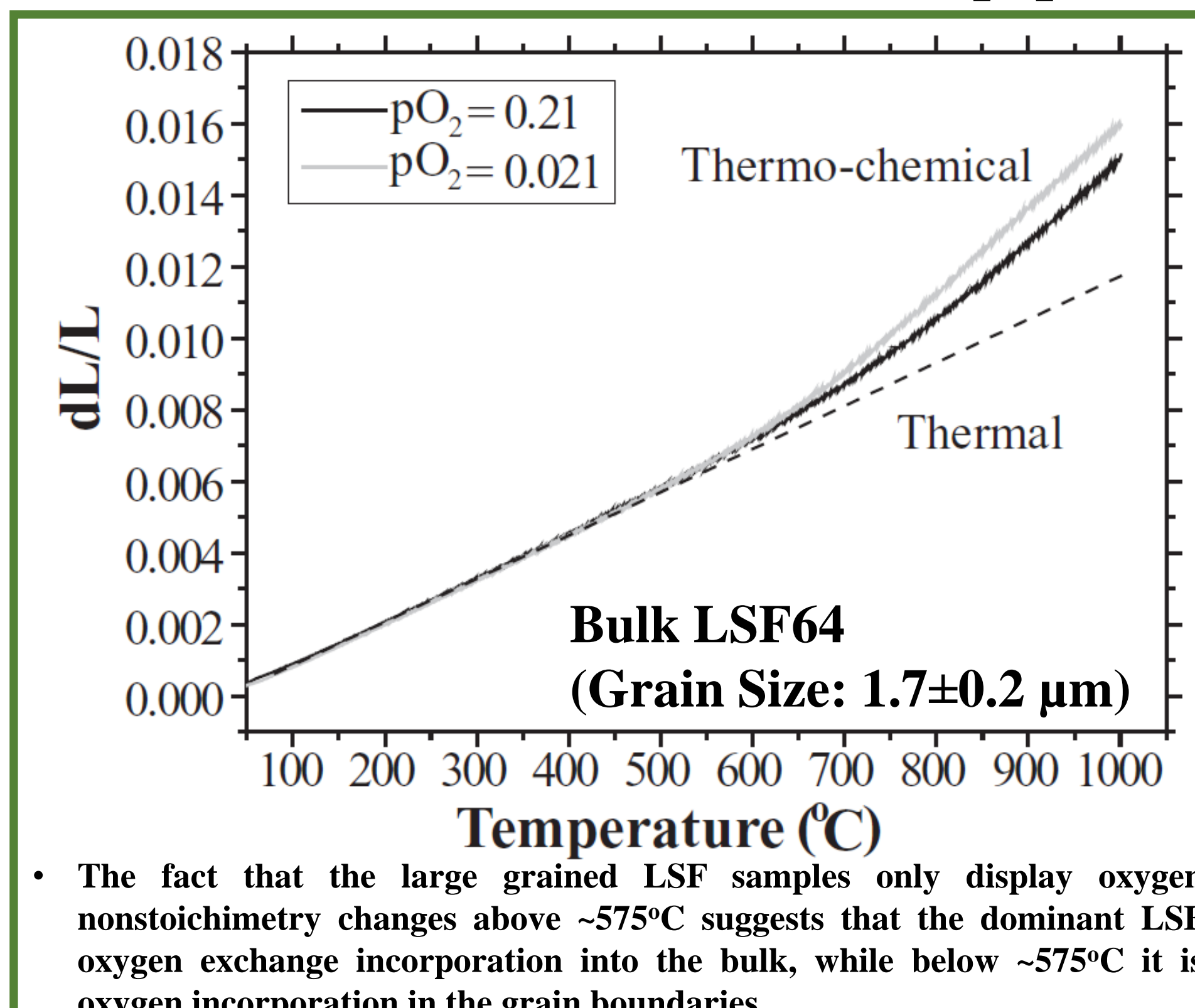
• A fast and a slow oxygen exchange process, presumably oxygen exchange into different crystallographic directions, are observed at all temperatures
• A transition in the dominant oxygen exchange mechanisms occurs at ~575°C

5. Chemical Stress



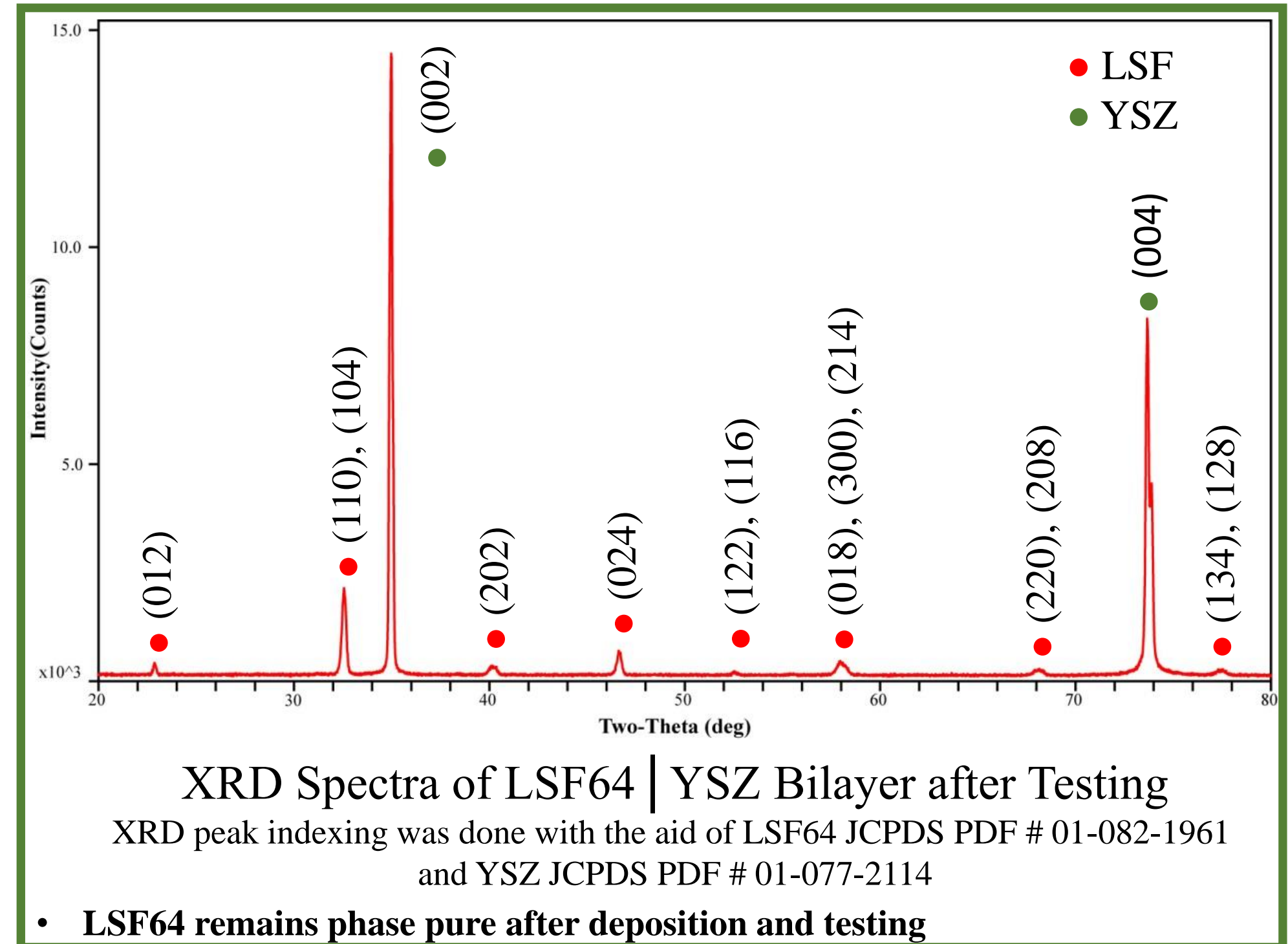
• A transition in the dominant chemical stress generating mechanism also occurs at ~575°C

6. Dilatometer Measurement [5]



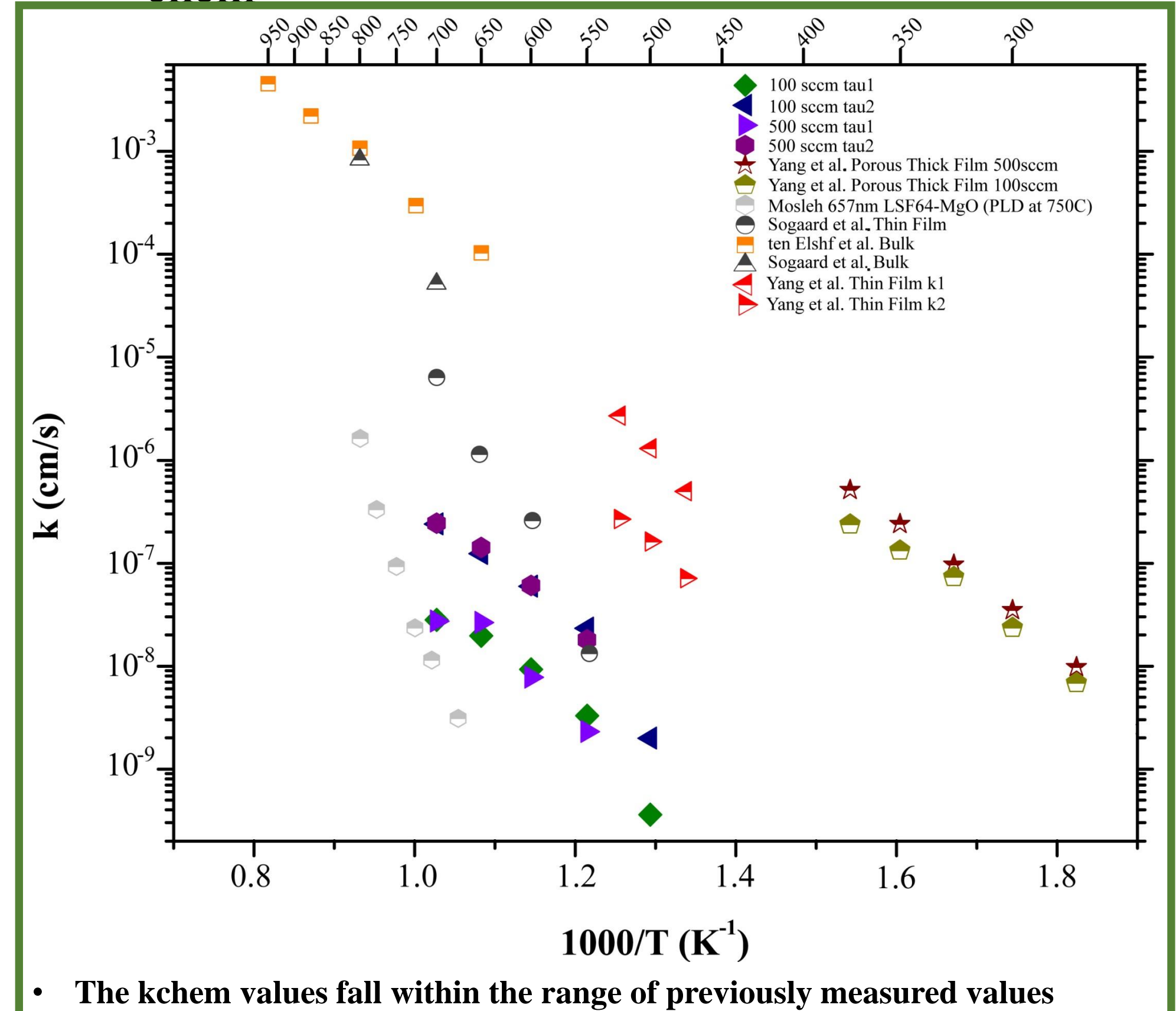
• The fact that the large grained LSF samples only display oxygen nonstoichiometry changes above ~575°C suggests that the dominant LSF oxygen exchange incorporation into the bulk, while below ~575°C it is oxygen incorporation in the grain boundaries

7. XRD Characterization



• LSF64 remains phase pure after deposition and testing

8. k_{chem} Literature Comparison [6-9]



• The k_{chem} values fall within the range of previously measured values

9. Conclusions

- Porous k_{chem} values can be obtained via a new, electrode-free, *in-situ* curvature relaxation technique.
- Two different physical processes, which are presumed to represent oxygen incorporation into the bulk above 575°C and into the grain boundary below 575°C, control the oxygen surface exchange coefficient and the chemical stress.
- While both bulk sample dilatometry and porous film chemical stress measurements detect changes in the bulk oxygen vacancy concentration at ~575°C and higher, the κR technique also detects oxygen vacancy concentration changes at lower temperatures due to its high resolution limit.
- In the future, the κR technique will be used to help identify self-passivating braze alloys by measuring the oxygen exchange kinetics of oxides forming on metal brazes.

10. References

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11. Acknowledgements

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